

In the Specification

Please replace the title “DEVICE FOR CONTROLLING A VOLTAGE-CONTROLLED POWER SWITCH” with the new title “DEVICE FOR CONTROLLING HIGH AND LOW LEVELS OF A VOLTAGE-CONTROLLED POWER SWITCH”.

Please replace the paragraph beginning on page 3, line 14 with the following amended paragraph:

According to an embodiment of the present invention, the device's circuit for setting to the low level comprises a second output terminal capable of being connected to the control terminal of the voltage-controlled switch and comprising: a seventh N-channel MOS transistor arranged between the second output terminal and the low voltage, and the gate of which is capable of being connected to the control block via the second controllable circuit breaker; and a limiting means controllable for, when the second circuit breaker is off, providing the gate of the seventh MOS transistor with an activation voltage as long as the voltage of the second output terminal is greater than a predetermined voltage ranging between the high and ground voltages; the control block enabling, upon activation of the Darlington assembly, provision of a deactivation signal to the gate of the seventh MOS transistor and, a second predetermined duration after the turning-off of the first circuit breaker:

- c/ deactivation of the Darlington assembly and turning off the second circuit breaker; and
- d/ after a third predetermined duration, turning on the second circuit breaker and providing an activation signal to the gate of the seventh MOS transistor.

Please replace the paragraph beginning on page 5, line 31 with the following amended paragraph:

According to a feature of the present invention, power transistor 2 is an NPN-type bipolar transistor and the control circuit of transistor 2 comprises an NPN-type bipolar transistor 3. Transistors 2 and 3 form a Darlington assembly: their collectors are connected to voltage V_h and their emitters are preferably connected to terminal OUTH, each by a resistor. The base of NPN power transistor 2 is connected to the emitter of NPN power transistor 3. The base of NPN control transistor 3 forms the control terminal of the Darlington assembly.

Please replace the paragraph beginning on page 10, line 4 with the following amended paragraph:

Circuit breaker 16 comprises a P-channel MOS transistor 36 having its source connected to the control terminal of the Darlington assembly and having its drain connected to the anode of diode D1. The gate of transistor 36 is connected via a resistor 38 to the drain of a P-channel MOS transistor 40. The source of transistor 40 is connected to voltage V_h . The gate of transistor 40 and is connected to the gate of transistor 4, so that transistor 40 forms a current mirror with transistor 4. The gate of transistor 36 is also connected to the anode of a zener diode 42 having its cathode connected to the anode of a zener diode 44 having its cathode connected to the control terminal of the Darlington assembly. The gate of transistor 36 is further connected to the anode of a diode 46 having its cathode connected to the control terminal of the Darlington assembly, and to the cathode of a diode 48 having its anode connected to the drain of transistor 40. A diode 50 has its anode connected to the drain of transistor 40 and its cathode connected to the drain of an N-channel MOS transistor 52 having its source connected to ground GND. The gate of transistor 52 is connected to block 30, for example, to receive control signal S16 illustrated in Fig. 2.